In the Claims:

1. (Currently amended) A polishing composition suitable for polishing semiconductor substrates having a non-ferrous interconnect comprising:

0.1 to 1.5 wt% of a polyvinyl alcohol; 0.01 to 0.85 wt% of polyvinylpyrrolidone;

up to 10 wt% of a corrosion inhibitor;

up to 15 wt% complexing agent;

up to 10 wt% of an oxidizing agent; and

0.05 to 40 wt% of an abrasive wherein the polishing composition has a pH of at least 7 and wherein increasing the weight ratio of the polyvinyl alcohol to the polyvinylpyrrolidone decreases the polishing removal rate of the non-ferrous interconnect.

2. (Previously presented) The composition of Claim 1, wherein the polyvinylpyrrolidone has a weight average molecular weight of 1,000 to 250,000 g/mole..

3. (Previously presented) The composition of Claim 1, wherein the abrasive particles include silica particles.

4. (Previously presented) The composition of Claim 1, wherein the polyvinyl alcohol has a weight average molecular weight of 1,000 to 1,000,000 grams per mole and a degree of hydrolyzation of at least 20 mole percent, wherein the mole percent is based upon the total number of moles of the polyvinylalcohol.

5. (Original) The composition of Claim 1, wherein the polyvinylpyrrolidone has a weight average molecular weight of 100 to 1,000,000 grams per mole.

6. (Original) The composition of Claim 1, wherein the polyvinylpyrrolidone and the thermoplastic polymer is present in the polishing composition in a weight ratio of 1:10 to 100:1 respectively.

7. (Currently amended) A polishing composition suitable for polishing semiconductor substrates having a nonferrous interconnect comprising:

0.1 to 1.5 wt% of polyvinyl alcohol having a weight average molecular weight of 3,000 to 500,000 g/mole;

0.01 to 0.85 wt% of polyvinylpyrrolidone having a weight average molecular weight of 1,000 to 250,000 g/mole;

up to 10 wt% of a corrosion inhibitor;

up to 15 wt% complexing agent;

up to 10 wt% of an oxidizing agent; and

0.1 to 40 wt% of a silica abrasive; wherein the polishing composition has a pH of at least 7, and further wherein increasing the weight ratio of the polyvinyl alcohol to the polyvinylpyrrolidone decreases the polishing removal rate of the non-ferrous interconnect.

8. (Previously presented) A method of polishing a semiconductor substrate having a non-ferrous interconnect comprising the steps of:

applying a polishing composition comprising 0.1 to 1.5 wt% of a polyvinyl alcohol; 0.01 to 0.85 wt% of polyvinylpyrrolidone; up to 10 wt% of a corrosion inhibitor; up to 15 wt% complexing agent; up to 10 wt% of an oxidizing agent; and 0.1 to 40 wt% of an abrasive wherein the polishing composition has a pH of at least 7; and

polishing the semiconductor substrate at a pad pressure less than or equal to 21.7 kiloPascals, wherein increasing the weight ratio of the polyvinyl alcohol to the polyvinylpyrrolidone decreases the removal rate of the non-ferrous interconnect.

9. (Original) The method of Claim 8, wherein the polishing composition facilitates a removal rate of less than or equal to 150 Angstroms/minute for the low-k dielectric layer.

10. (Original) The method of Claim 8, wherein the polishing composition facilitates a removal rate of greater than or equal to 150 Angstroms/minute for the low-k dielectric layer.